RENESAS

Data Sheet

NP90N055VUK

MOS FIELD EFFECT TRANSISTOR

R07DS0578EJ0100
Rev.1.00
Nov 29, 2011

Description

The NP90N055VUK is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Super low on-state resistance
  $R_{DS(on)}$ = 3.85 mΩ MAX. (V_{GS} = 10 V, I_D = 45 A)
- Low C_{iss}: C_{iss} = 4000 pF TYP. (V_{DS} = 25 V)
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing		Package
NP90N055VUK-E1-AY *1	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	TO-252 (MP-3ZP)
NP90N055VUK-E2-AY *1			Taping (E2 type)	

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V_{GS} = 0 V)	V_{DSS}	55	V
Gate to Source Voltage (V_{DS} = 0 V)	V_{GSS}	±20	V
Drain Current (DC) (T_C = 25°C)	$I_{D(DC)}$	±90	A
Drain Current (pulse) *1	$I_{D(pulse)}$	±360	A
Total Power Dissipation (T_C = 25°C)	P_{T1}	147	W
Total Power Dissipation (T_A = 25°C)	P_{T2}	1.2	W
Channel Temperature	T_{ch}	175	°C
Storage Temperature	T_{stg}	–55 to 175	°C
Repetitive Avalanche Current *2	I_{AR}	33	A
Repetitive Avalanche Energy *2	E_{AR}	108	mJ

Notes: *1 T_C = 25°C, $P_W \le 10$ μs, Duty Cycle ≤ 1%
*2 R_G = 25 Ω, V_{GS} = 20 → 0 V

Thermal Resistance

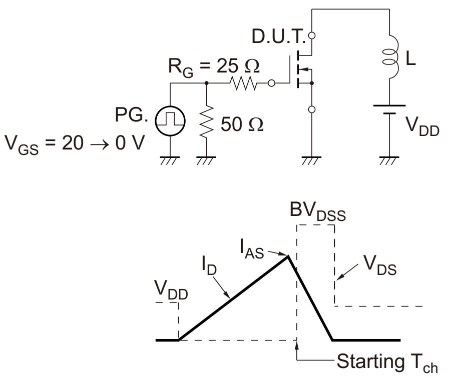
Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.02	°C/W
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	125	°C/W

Electrical Characteristics (T_A = 25℃)

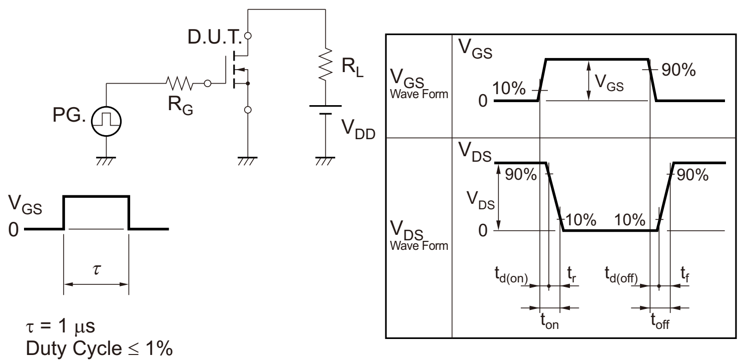
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 55 V, V_{GS} = 0 V
Gate Leakage Current	I_{GSS}	—	—	±100	nA	V_{GS} = ±20 V, V_{DS} = 0 V
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	V_{DS} = V_{GS}, I_D = 250 μA
Forward Transfer Admittance *1	$\mid y_{fs} \mid$	30	60	—	S	V_{DS} = 5 V, I_D = 45 A
Drain to Source On-state Resistance *1	$R_{DS(on)}$	—	3.20	3.85	mΩ	V_{GS} = 10 V, I_D = 45 A
Input Capacitance	C_{iss}	—	4000	6000	pF	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz
Output Capacitance	C_{oss}	—	410	620	pF	
Reverse Transfer Capacitance	C_{rss}	—	150	270	pF	
Turn-on Delay Time	$t_{d(on)}$	—	25	60	ns	V_{DD} = 28 V, I_D = 45 A, V_{GS} = 10 V, R_G = 0 Ω
Rise Time	t_r	—	10	30	ns	
Turn-off Delay Time	$t_{d(off)}$	—	65	130	ns	
Fall Time	t_f	—	6	20	ns	
Total Gate Charge	Q_G	—	68	102	nC	V_{DD} = 44 V, V_{GS} = 10 V, I_D = 90 A
Gate to Source Charge	Q_{GS}	—	18	—	nC	
Gate to Drain Charge	Q_{GD}	—	18	—	nC	
Body Diode Forward Voltage *1	$V_{F(S-D)}$	—	0.9	1.5	V	I_F = 90 A, V_{GS} = 0 V
Reverse Recovery Time	t_{rr}	—	47	—	ns	I_F = 90 A, V_{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q_{rr}	—	80	—	nC	

Note: *1 Pulsed test

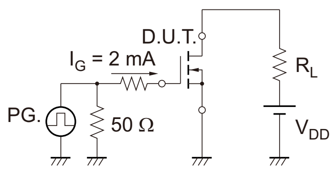
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

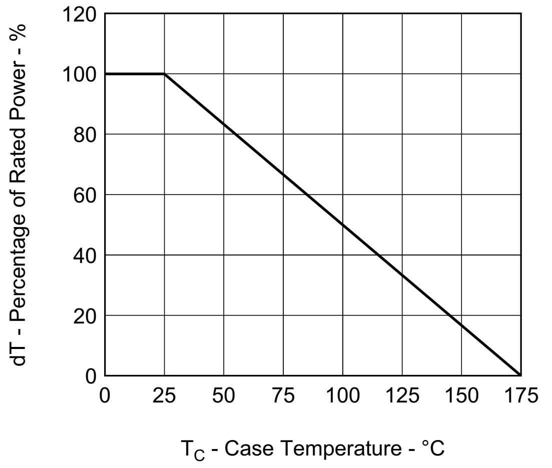


TEST CIRCUIT 3 GATE CHARGE

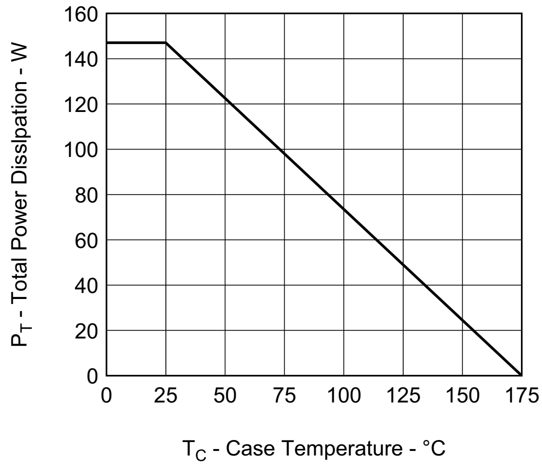


Typical Characteristics (T_A = 25℃)

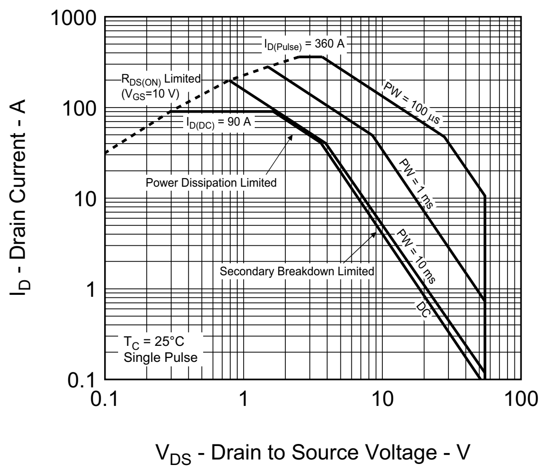
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



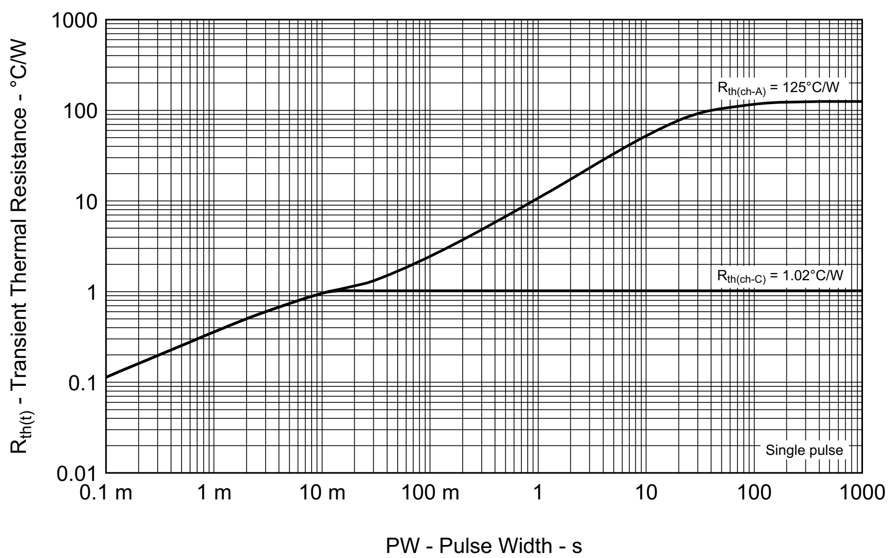
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

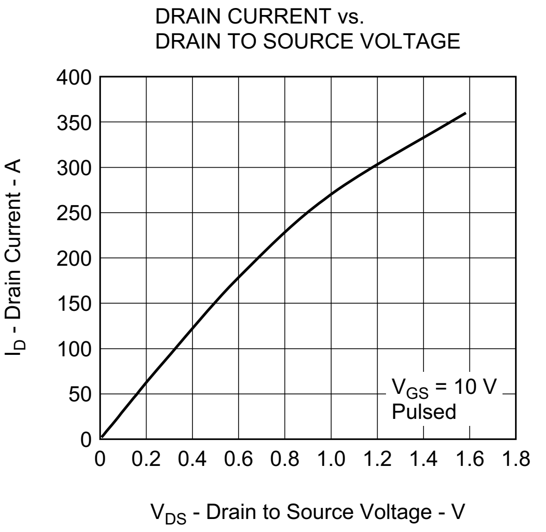


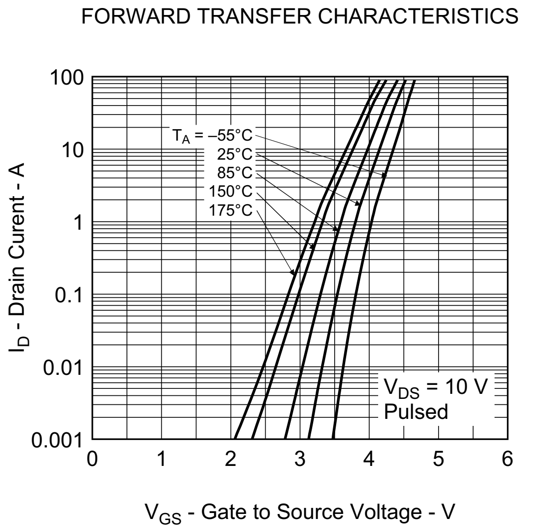
FORWARD BIAS SAFE OPERATING AREA

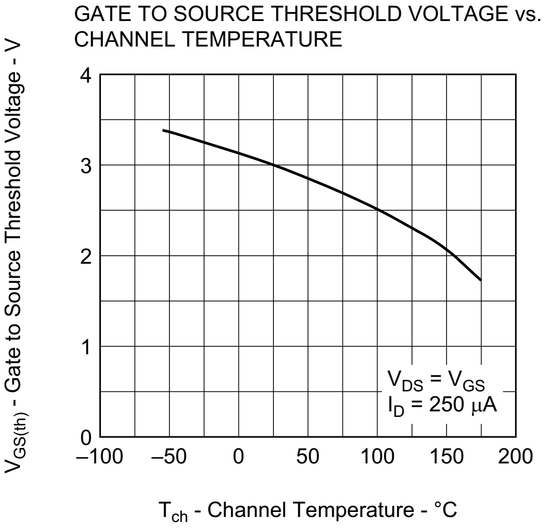


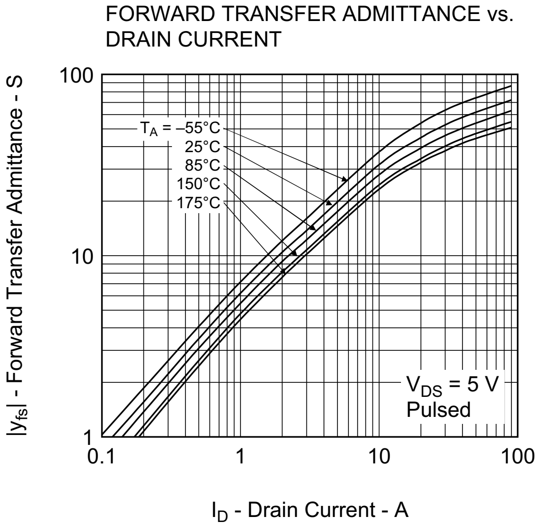
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

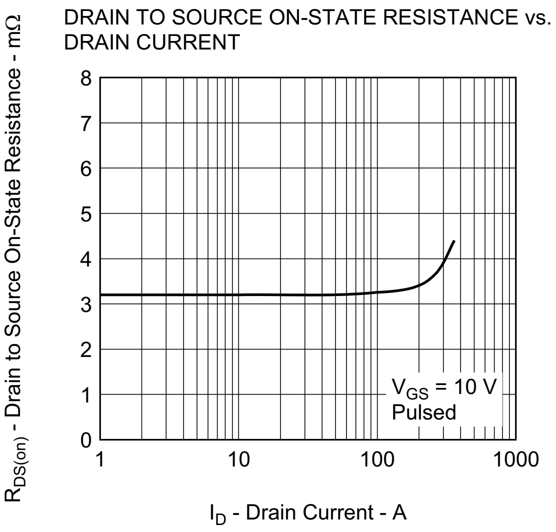


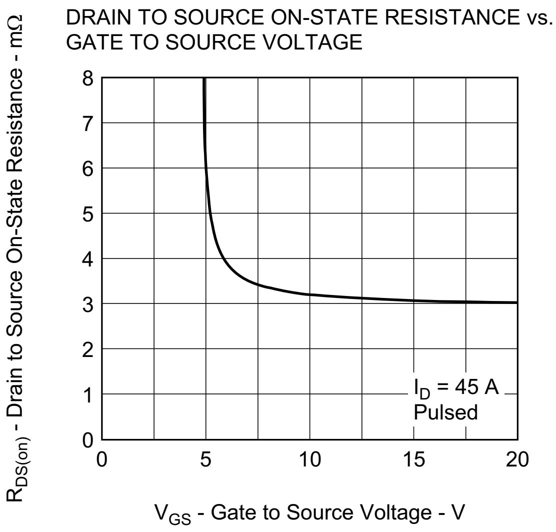

DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE
I_D - Drain Current - A
V_DS - Drain to Source Voltage - V
V_GS = 10 V
Pulsed


FORWARD TRANSFER CHARACTERISTICS
I_D - Drain Current - A
V_GS - Gate to Source Voltage - V
T_A = –55°C
25°C
85°C
150°C
175°C
V_DS = 10 V
Pulsed

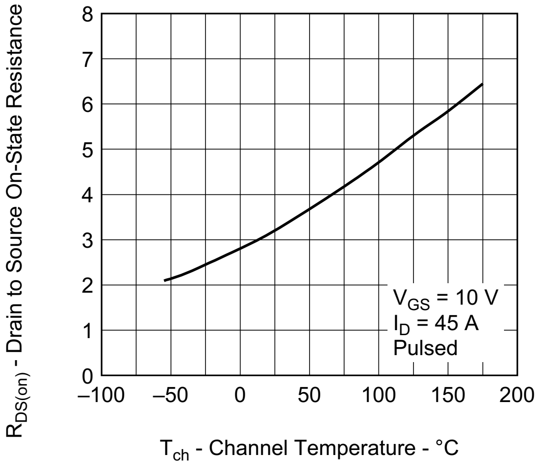

GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATURE
V_GS(th) - Gate to Source Threshold Voltage - V
T_ch - Channel Temperature - °C
V_DS = V_GS
I_D = 250 μA


FORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENT
|y_fs| - Forward Transfer Admittance - S
I_D - Drain Current - A
T_A = –55°C
25°C
85°C
150°C
175°C
V_DS = 5 V
Pulsed

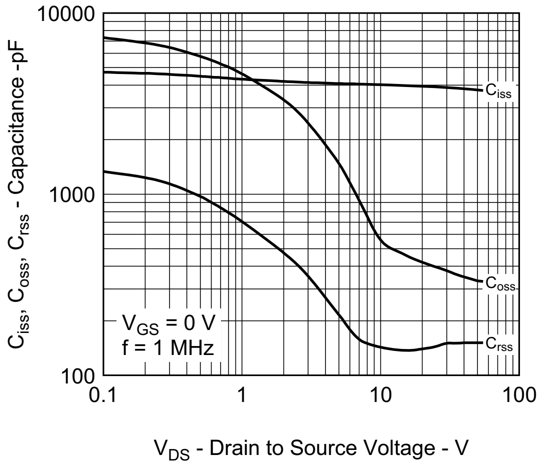

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENT
R_DS(on) - Drain to Source On-State Resistance - mΩ
I_D - Drain Current - A
V_GS = 10 V
Pulsed


DRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE
R_DS(on) - Drain to Source On-State Resistance - mΩ
V_GS - Gate to Source Voltage - V
I_D = 45 A
Pulsed

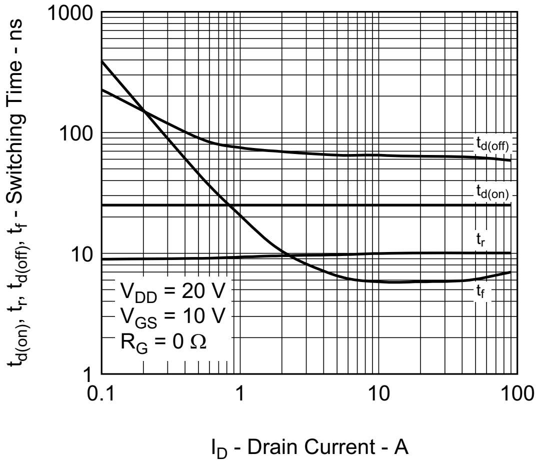
DRAIN TO SOURCE ON-STATE RESISTANCE vs.
CHANNEL TEMPERATURE



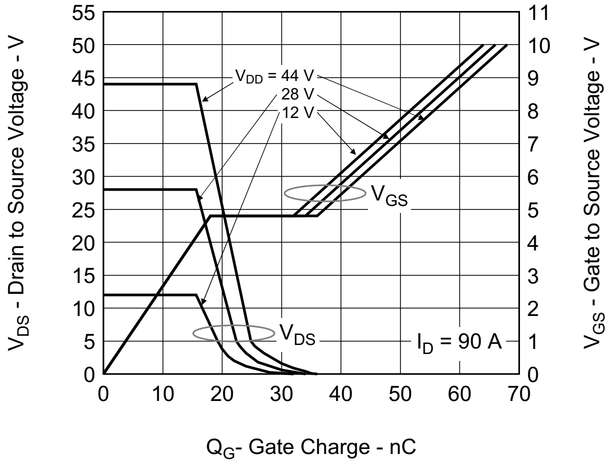
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



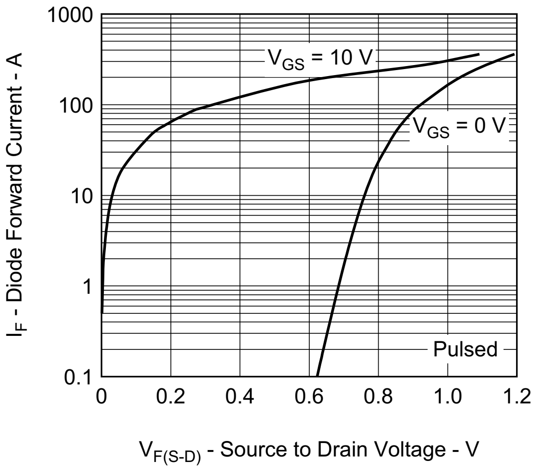
SWITCHING CHARACTERISTICS



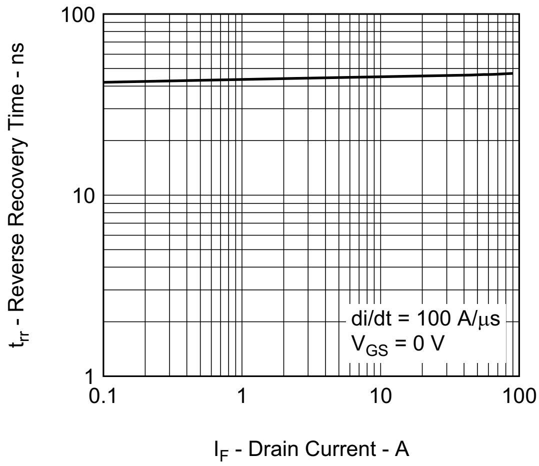
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

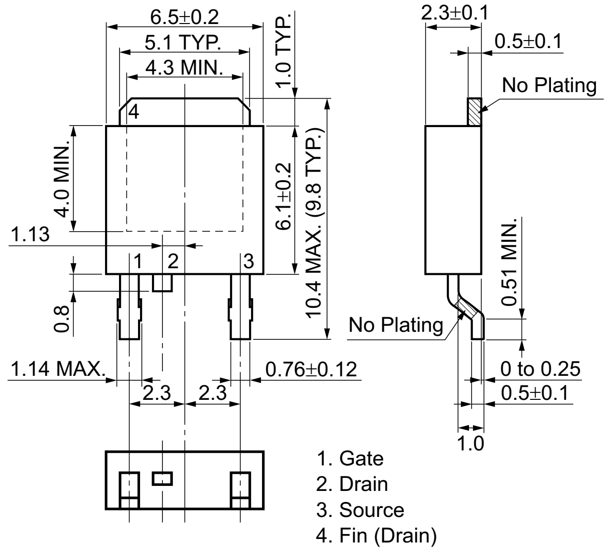


REVERSE RECOVERY TIME vs.
DRAIN CURRENT

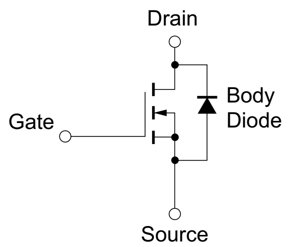


Package Drawing (Unit: mm)

TO-252 (MP-3ZP) (Mass: 0.27 g TYP.)



Equivalent Circuit



Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History	NP90N055VUK Data Sheet

Rev.	Date	Description	
		Page	Summary
1.00	Nov 29, 2011	—	First Edition Issued

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